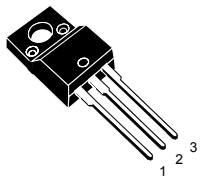
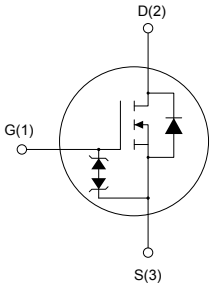
STF7N60M2

Datasheet

N-channel 600 V, 860 mΩ typ., 5 A MDmesh M2 Power MOSFET in a TO-220FP package



TO-220FP



AM01476v1

Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STF7N60M2	600 V	950 mΩ	5 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- Very low turn-off switching losses
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Product status link
STF7N60M2

Product summary	
Order code	STF7N60M2
Marking	7N60M2
Package	TO-220FP
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	5	A
I_D	Drain current (continuous) at T_C = 100 °C	3.5	A
I_{DM}(1)	Drain current (pulsed)	20	A
P_{TOT}	Total power dissipation at T_C = 25 °C	20	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)	2.5	kV
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
dv/dt(3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Operating junction temperature range		°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 5 A, di/dt ≤ 400 A/µs, V_{DS} (peak) < $V_{(BR)DSS}$, V_{DD} = 400 V.*
3. *V_{DD} = 400 V.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	6.25	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	1.5	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	99	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	600	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V	-	-	1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_C = 125 °C(1)	-	-	100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V	-	-	±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 2.5 A	-	860	950	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	271	-	pF
C_{oss}	Output capacitance		-	15.7	-	pF
C_{rss}	Reverse transfer capacitance		-	0.68	-	pF
$C_{oss\ eq.}$(1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	75.5	-	pF
R_g	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	7.2	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 5 A, V_{GS} = 0 to 10 V (see the Figure 14. Test circuit for gate charge behavior)	-	8.8	-	nC
Q_{gs}	Gate-source charge		-	1.8	-	nC
Q_{gd}	Gate-drain charge		-	4.3	-	nC

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 2.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see the Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	7.6	-	ns
t_r	Rise time		-	7.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	19.3	-	ns
t_f	Fall time		-	15.9	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	5	A
I_{SDM}(1)	Source-drain current (pulsed)		-	-	20	A
V_{SD}(2)	Forward on voltage	I_{SD} = 5 A, V_{GS} = 0 V	-	-	1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 5 A, di/dt = 100 A/µs, V_{DD} = 60 V (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	275	-	ns
Q_{rr}	Reverse recovery charge		-	1.55	-	µC
I_{RRM}	Reverse recovery current		-	11	-	A
t_{rr}	Reverse recovery time	I_{SD} = 5 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_J = 150 °C (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	376	-	ns
Q_{rr}	Reverse recovery charge		-	2.1	-	µC
I_{RRM}	Reverse recovery current		-	11	-	A

1. *Pulse width limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

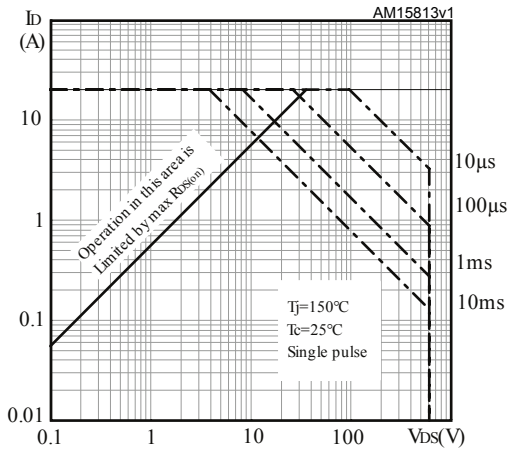


Figure 2. Normalized transient thermal impedance

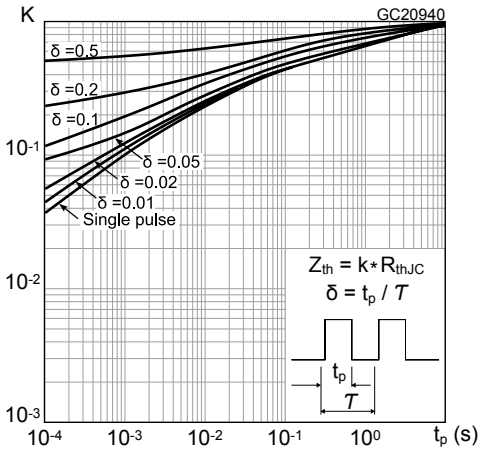


Figure 3. Typical output characteristics

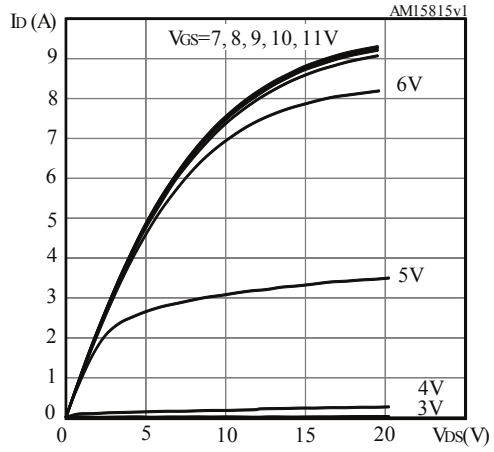


Figure 4. Typical transfer characteristics

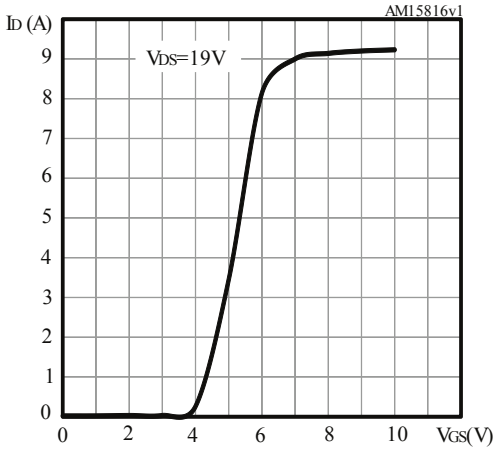


Figure 5. Typical gate charge characteristics

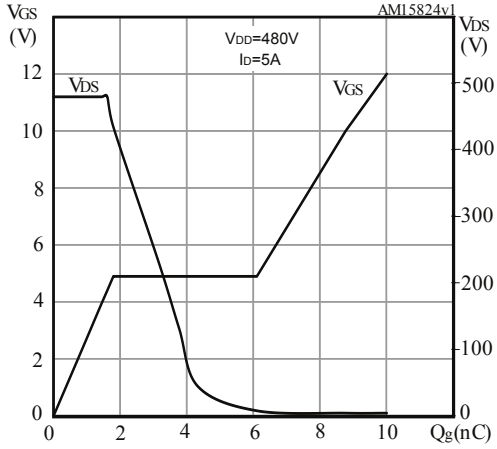


Figure 6. Typical drain-source on-resistance

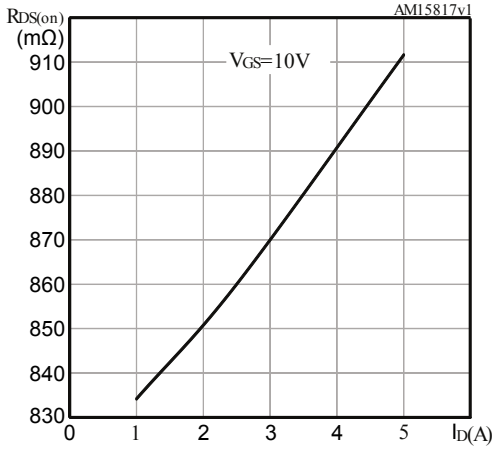


Figure 7. Typical capacitance characteristics

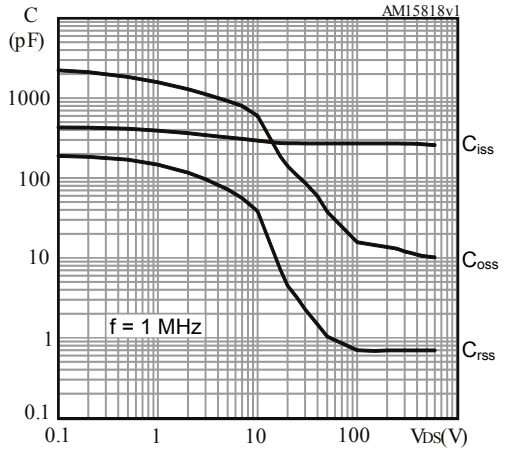


Figure 8. Typical output capacitance stored energy

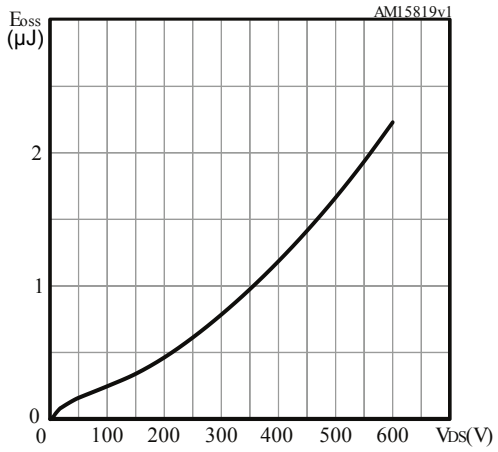


Figure 9. Normalized gate threshold vs temperature

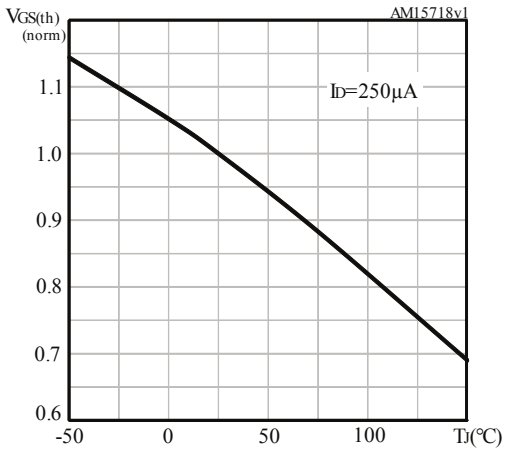


Figure 10. Normalized on-resistance vs temperature

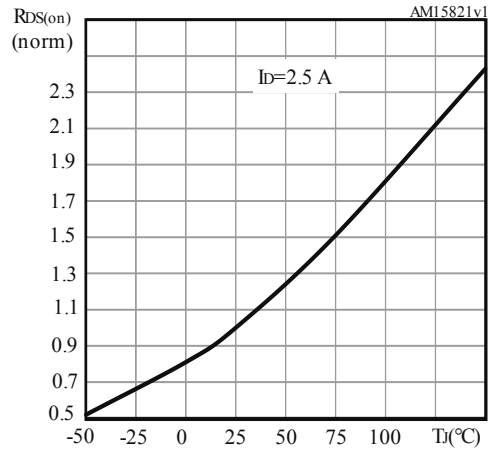


Figure 11. Normalized breakdown voltage vs temperature

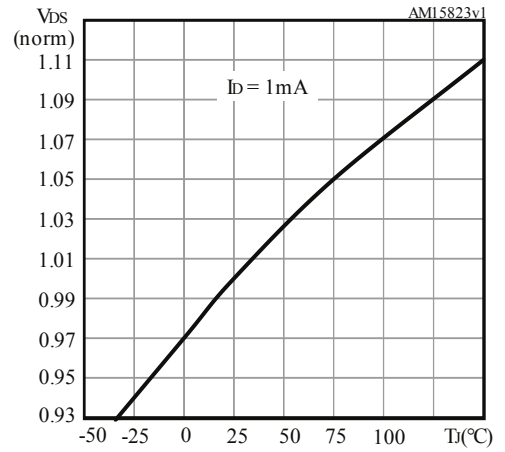
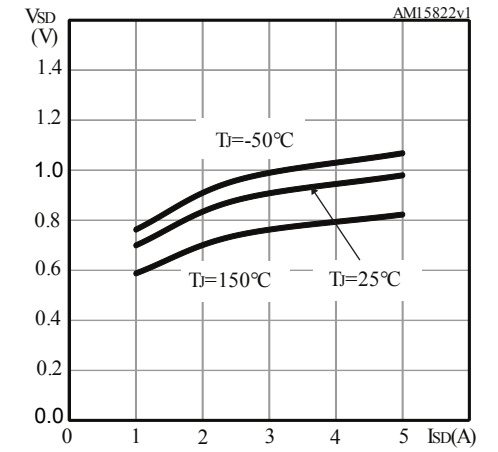
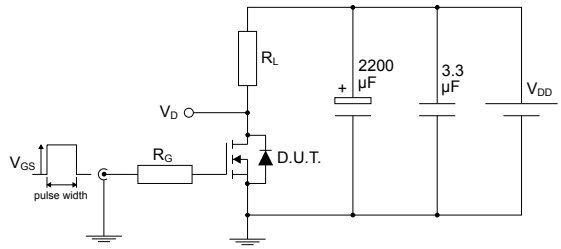


Figure 12. Typical reverse diode forward characteristics



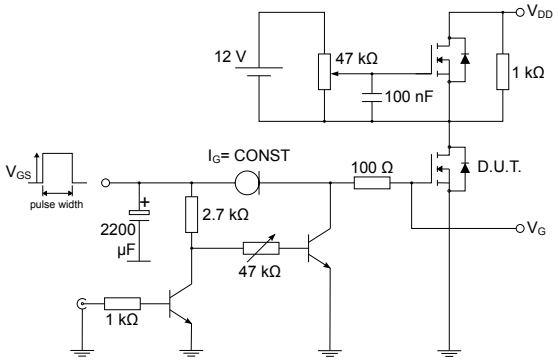
3 Test circuits

Figure 13. Test circuit for resistive load switching times



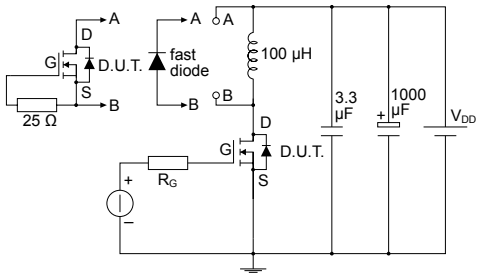
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Figure 14. Test circuit for gate charge behavior



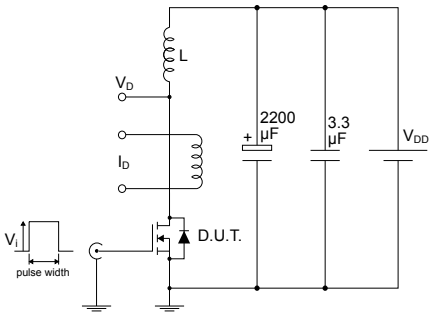
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Figure 15. Test circuit for inductive load switching and diode recovery times



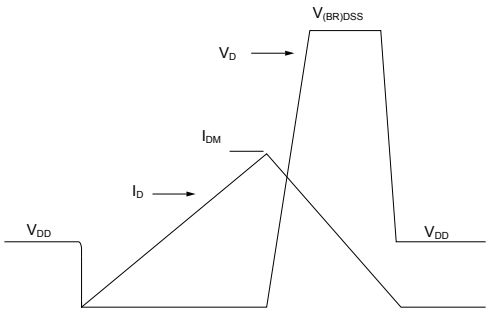
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Figure 16. Unclamped inductive load test circuit



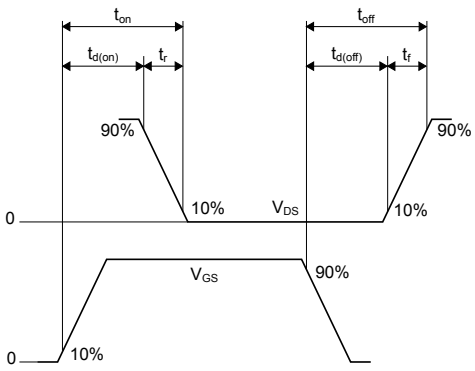
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Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP type B package information

Figure 19. TO-220FP type B package outline

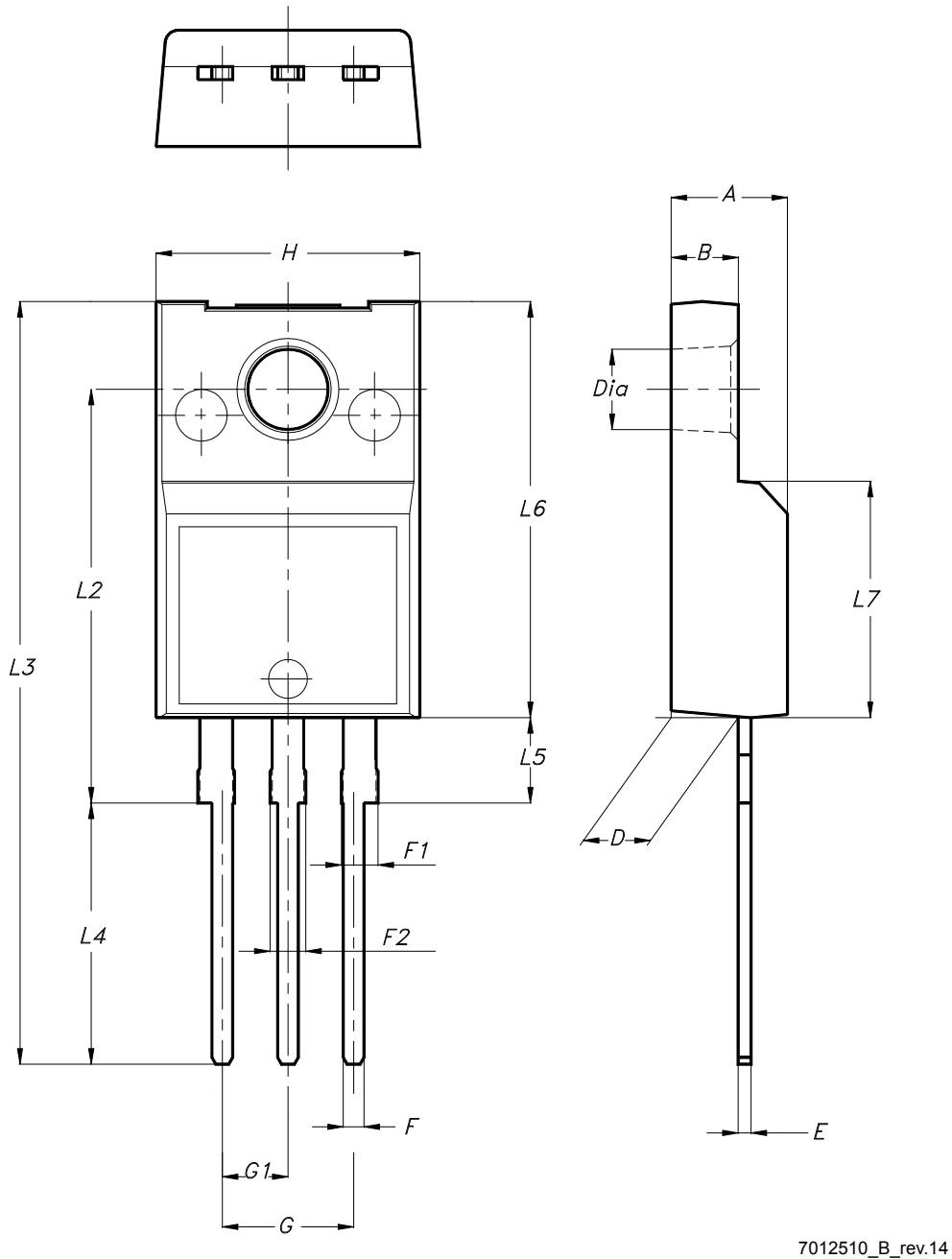


Table 8. **TO-220FP type B package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

Revision history

Table 9. **Document revision history**

Date	Revision	Changes
26-Jun-2013	1	First release.
08-Apr-2026	2	Updated Section 4: Package information. Minor text changes.

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